Spatial decay of the single-particle density matrix in tight-binding metals: analytic results in two dimensions

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A nalytical results for the asymptotic spatial decay of the density matrix $(r;r^0)$ in the tightbinding model of the two-dimensional metal are presented. In various dimensions D, it is found analytically and numerically that the density matrix decays with distance according to the power law, $(r;r^0) / jr r^0 j^{(D+1)=2}$.

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The computation of ground-state properties of a condensed-matter system from the electronic structure depends critically upon the computation of the singleparticle density matrix (DM). If one possesses the occupied eigenstates i (r) of a single-particle H am iltonian \hat{H} , then the density matrix at zero temperature can be i_{occupied} i (r⁰) i (r). The diexpressed as $(r; r^0) =$ agonal element of the DM, (r;r), is the charge density. The electronic energy may be expressed as ${\rm Tr}(\hat{\ }\hat{H}$), and in a simple case the electronic part of the interatom ic forces may be expressed as $Tr(\ \Cellet = \Cellet R)$, where R is an atom ic coordinate. Viewed in the position representation, it is clear that the decay of $(r;r^{0})$ determ ines how locally one can formulate a calculation of the energy or forces. This is of special interest in so-called "quantum order-N" methods in modern rst-principles computational condensed-m atter physics [1, 2].

The DM provides a means to di erentiate between a m etallic and an insulating state. A considerable body of work has been devoted to computing the DM in various system s. For insulators, it is well established that, for $\dot{\mathbf{j}}$ $^{0}\mathbf{j}$ [3, 4]. Recently, ŕ $r_{j}! 1$, (r; r_{i}) exp (we have published detailed asym ptotic expansions for insulators in one, two and three dimensions [5]. In metals the situation is less clear. A nalytic results are available for the free-electron gas in any dimensionality $(D = 1 \ 3)$ and the DM exhibits a power-law decay with Gibbs ringing (from the abrupt cuto at the Ferm is array T = 0) [6]. Little is known about the \tight-binding" case, except in one dimension where the mathematics is trivial. One more \realistic" num erical calculation with a density functional Ham iltonian has appeared for Al, which produces a DM quite sim ilar to the free-electron gas[7]. In this Brief Report, we provide analytical asymptotic results for the decay of the DM in one dimension and, for the rst time, in two dimensions for special directions on a square lattice. The DM is found to decay gener $r^0 j^{(D+1)=2}$ for large jr $r^0 j$ which coincides ally as †r with the free-electron case. Num erics support this law for all three dimensions along various lattice directions.

W e provide detailed expressions for the decay depending upon the param eters of the one-band tight-binding m odel and the position of the Ferm i level. The analytic results are con rm ed by direct num erical evaluation of the DM.

Let us consider a tight-binding H am iltonian de ned on a lattice,

$$\hat{H} = \begin{bmatrix} X^{N} & X^{N} \\ & &$$

where the orthonorm al site basis jii (one electron orbital per site) spans the Hilbert space of the state vectors. In the case analyzed below, all the site energies, "i = ", and transfer integrals between nearest neighbours, $t_{ij} = t$, are constant through the lattice. The B loch functions, $t_{ki} = N^{1-2}$ j expfik Bgjji, with dispersion " $_{k} = 2t^{P_{D}} \cos(k a)$ for the simple cubic lattice (say, with lattice constant a = 1 and "= 0) solve the eigenproblem for the Ham iltonian (1).

The object to evaluate is the density-matrix operator, ^, which can be written in the momentum representation as ^= $_{k}$; k if $_{k}$ hk j w ith f_{k} being the occupation probabilities for di erent eigenstates. For an electronic system in therm alequilibrium, these probabilities are the Ferm i-D irac factors, $f_k = f("_k) = (1 + \exp [("_k$ $)=T])^{1}$ is the Ferm i level and T is the tem perature. where The matrix elements of the density-matrix operator in the site basis, ii = hij^jji, are of special interest for obtaining the decay properties of the DM in real space. These matrix elements can be written in term softhem atrix elements of the G reen's function operator, G_{ij} (") = Ĥ)¹ jji, as: hij("

The problem of the DM decay is thus partly reduced to the problem of the evaluation of the o -diagonal elements

of the G reen's function operator in the site basis, which is known to be not at all an easy task (see e.g. Ref. [8] and references therein). A fler some standard algebraic manipulations and introducing auxiliary integration (see e.g. [9]), the expression for G_{ij} G for the simple cubic lattice can be recast in the following form :

G (") =
$$\frac{i}{2t} \begin{bmatrix} z_1 \\ expfiz \\ 0 \end{bmatrix} = 2tg \quad i \quad J \quad (z)dz;$$
 (3)

where the integers for the Cartesian projections of the connection vector R $_j$ R $_i$, and J (z) is the Bessel function.

Starting from this point, we are able to proceed analytically further only in the particular case of a square lattice (D = 2) along the main diagonal, x = y (and in the one-dimensional case as well), when the integral over z can be taken exactly [10]:

Z₁
expfiz"=2tgJ²(z)dz =
$$\frac{1}{-Q}$$
 (1 2²) + $\frac{i}{2}P$ (1 2²); (4)

if the energy belongs to the band region, 0 < j j < 1, where "=4t. The functions P and Q are the associated Legendre functions of the rst and second kind, respectively. The expression for the DM can then be recast as

$$= (1) \frac{2}{2} \int_{1}^{Z} Q_{1=2} (1 Q^{2}) d; \qquad (5)$$

where $_{\rm F}$ =4t is the dimensionless Ferm i level and the zero-tem perature case is in plied. If the Ferm i level lies above the band, i.e. $_{\rm F}$ 1, all the states are occupied at zero tem perature and the DM is = $_0$, just re ecting the completeness of the basis set. This property, together with the even character of the integrand in Eq. (5), allow s us to rewrite the expression for the DM (for > 0) in the following form :

$$= (1) \frac{2}{0} \sum_{p=1}^{\infty} Q_{1=2} (1 2^{2}) d; \qquad (6)$$

and consider for de niteness only $_{\rm F} > 0$.

The integral in Eq. (6) can be simplied in the asymptotic limit of large ! 1 by using the asymptotic expression for Q $_{1=2}$ (cos) [10],

$$Q_{1=2}(\cos)' \frac{r}{2 \sin} \cos + \frac{1}{4};$$
 (7)

where $= \cos^{1} (1 2^{2})$, so that

$$' \frac{(1)}{2^{3=2}} \int_{0}^{2} \frac{\sin \pi}{1 \cos 2} \cos \pi + \frac{1}{4} d ; (8)$$

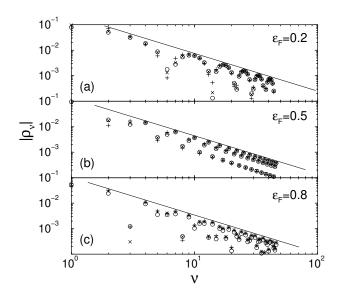


FIG.1: The dependence of the absolute value of the DM, j j on the lattice index along the main diagonal [1;1] in the square lattice (R_j R_j = (x; y) (;)) for a tight-binding model of a crystalline m etal at zero tem perature and various positions of the Ferm i-level, $_{\rm F}$ = =4t, as marked in (a)-(c). The open circles represent the exact num erical result obtained from Eq. (2). The crosses and pluses correspond to the approximate results obtained by using Eqs. (9) and (11), respectively. The straight solid lines show the power-law dependence, / $^{3=2}$.

with $_0 = \cos^1 (1 2_F^2)$. The nal step revealing the explicit asymptotic dependence of the DM on can be made if the Fermi level lies not far from the midband point and $_0$ 1. In that case, the rst term of the integrand in Eq. (8) can be expanded in , resulting in

$$(1) \frac{p_{\overline{2}}}{3-2} \int_{0}^{Z} \cos^{2} + \frac{1}{4} d;$$
 (9)

with $_0 = \overset{F}{} \underbrace{}_0$. All the non-trivial dependence on is now in the upper limit of the integral, the latter being proportional to the Fresnel integrals C (x) and S (x),

$$'(1) - \frac{1}{p_{2}}^{h} C(2_{0}) =) S(2_{0}) + \frac{1}{2} C(2_{0}) + \frac{$$

and in the asymptotic limit, $p_{20} = ! 1 [10]$,

,

$$(1) \frac{1}{()^{3=2} p_{\overline{2} 0}} \cos 0 \frac{1}{4} : (11)$$

As follows from Eq. (11), the DM decays according to the power law, $_{\rm ij}$ / $R_{\rm j}$ $R_{\rm i} j^{\,3=2}$, at least along the main diagonal in the square lattice.

All the analytical results presented above can be veri ed by direct num erical analysis. In Figs. 1(a)-(c), we show the dependence of the DM versus along the diagonal [1;1] in the square lattice for di erent positions of the Ferm i level. The exact num erical results (open circles) have been obtained by both direct sum m ation over

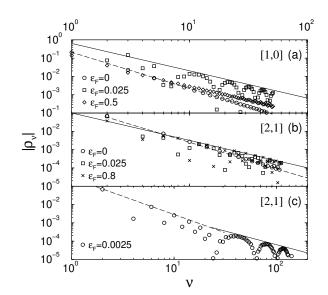


FIG.2: The dependence of the absolute value of the DM, j j on the lattice index : (a) along the direction [1;0] in the square lattice (R_j R_j = ($_x$;0) (;0)) and (b)-(c) along the direction [2;1] in the square lattice (R_j R_j = ($_2$ y; y) (2;)) for the same m odel as in Fig. 1. The results are obtained numerically from Eq. (2). The straight solid and dashed lines show the power-law dependences, / $^{3=2}$ and / 2 , respectively.

the rst Brillouin zone in Eq. (2) (over 10^8 points) and by integration of Eq. (5) (both m ethods give identical results). The approximate analytic results according to Eqs. (9) and (11) are given by the crosses and pluses, respectively. G ood agreement between the exact and approximate dependencies is evident, even for the relatively large values of the Ferm i-level position far away from the m idband region (see Fig. 1 (c)). The solid straight lines in Fig. 1 corresponding to the power law, j j/ $^{3=2}$, con m the same law for the DM decay.

In order to verify the power-law decay of the DM along other directions in the sim ple square lattice, we have calculated the DM num erically for these directions and have found the same asymptotic behavior, / $^{3=2}$. The results for directions [1;0] and [2;1] and di erent positions of the Ferm i level are presented in Figs. 2 (a)-(c).

For the special case that the Ferm i level lies exactly at the band center, $_{\rm F} = 0$, note that for the main diagonal [1;1], the DM vanishes for > 0 (see Eq. (6)). This behavior is also manifested in other directions: for $_{\rm F} = 0$ from $/ \frac{3=2}{2}$ to $/ \frac{2}{2}$ (see the dashed lines in F igs. 2 (a)-(b)). Fig. 2 (c) shows how this occurs for the direction [2;1] when $_{\rm F}$! 0.

The analysis of the DM decay in di erent dimensions can be performed analytically for D = 1 and numerically for D = 3. First, we bok at the one-dimensional system. In the case of zero temperature, the integrals in Eq. (2) can be taken exactly, resulting in the following expression

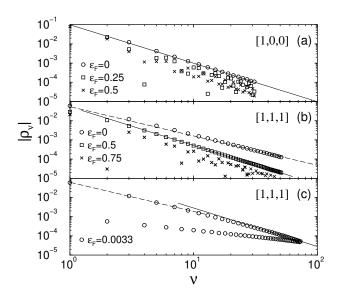


FIG.3: The dependence of the absolute value of the DM, j j on the lattice index : (a) along the direction [1;0;0] in the sim ple cubic lattice (R j R j = ($_x$;0;0) (;0;0)) and (b)-(c) along the direction [1;1;1] in the sim ple cubic lattice (R j R j = ($_x$; y; z) (;;)) for a tight-binding m odel of a crystalline m etal at zero tem perature and various positions of the Fermi level, $_F$ = =8t, as m arked. The results are obtained num erically from Eq. (2). The straight solid and dashed lines show the power-law dependences, / 2 and / $^{3-2}$, respectively.

for the DM (j = 2tj 1):

$$= \frac{1}{-1} \sin^{h} \sin^{1} \frac{1}{2t} + \frac{1}{2} : \qquad (12)$$

This expression has the correct limits for a fully occupied (=2t) and an empty (=2t) band, viz. $=_{0}$ and = 0, respectively, and shows the power-law decay, $/^{1}$. Bearing in mind the decay law, $/^{3=2}$, found for D = 2, we can infer that the generalized law in all dimensions is:

$$\mu_{ij} = / (D + 1) = 2 / R_j R_i j^{(D + 1) = 2}$$
: (13)

In order to check Eq. (13) for D = 3, we have calculated numerically the DM for the simple cubic lattice along di erent directions for various positions of the Ferm i level. The results are shown in Figs. 3 (a)-(c), from which it is clear that indeed the DM asymptotically satisfies Eq. (13) and / 2.

Sim ilar to the 2D -case, the m id-band location of the Ferm ienergy brings additional sym m etry to the problem which can change the asymptotic behaviour of the DM along certain directions. For example, if $_{\rm F}$ = 0 then

= 0 for > 0 along the direction [1;1;0] and / $^{3=2}$ along the [1;1;1] direction (see the dashed line in Fig.3(b); Fig.3(c) dem onstrates how the new asymptotic behavior appears when the Ferm i level approaches the midband position).

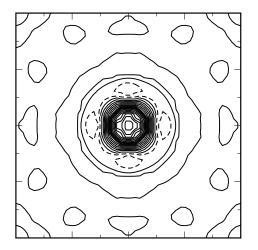


FIG.4: Contour plot of the real-space density m atrix for Al calculated in the fl00g plane for the conventional cubic unit cell (the x y axes are parallel to the bonds).

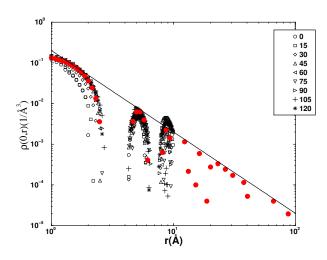


FIG. 5: Spatial decay of the real-space density matrix for Alcalculated for di erent angular directions, as marked (zero angle refers to the bond direction), in the fl00g plane for the conventional cubic unit cell. The solid circles represent calculated values of the density matrix for the free-electron gas model with the same electron density as for Al. The solid line shows an r² dependence.

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The above analytical and num erical results have been obtained for very simple tight-binding models. This of course leaves open the question about the generality of our ndings. In order to answer this question, at least to som e extent, we have calculated the single-electron DM for a realistic model of fcc alum inum (500 atom supercell with the box side of 20:25rA) using an approximate density functional Ham iltonian in the local density approximation (see Ref. [7] for more detail). The results are presented in Figs. 4 and 5. The real-space contour plot for the DM in the f100g plane for the conventional cubic unit cell is shown in Fig. 4. From this plot, we can see the isotropic m etallic nature of the bonding, in contrast to the case of sem iconductors with covalent bonding (cf. Fig. 3 in Ref. [7]). The spatial decay of the DM along di erent directions in the sam e sym m etry plane for Alis shown in Fig. 5, together with the data calculated for the free-electron gas m odel [6] (with the electron density being the same as that for Al, i.e. 0.185rA^{-3}). It is clearly seen that the DM for Aldecays in a very sim ilar fashion to that for the free-electron gas model, i.e. $/ r^2$. Therefore, these results support the generality of our model calculations.

In conclusion, we have presented analytical and numerical arguments supporting the power-law decay of the density matrix, $_{ij} / \Re_j R_{ij} (D^{+1)=2}$, in tight-binding models of metals in dimensions at zero temperature. The main result is the analytical asymptotic dependence of the density matrix versus distance along the main diagonal in the square lattice (see Eq. (11)). Apparently, the sharp cuto induced by the Ferm iD irac distribution at zero temperature in the integration over the energy spectrum, independently of the shape of the density of states, results in the power-law decay of the density matrix in crystalline metals.

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